Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low leakage current
- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.0 × 0.6 × 0.48 mm
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance R_{DSon} = 1.02 Ω

3. Applications

- Relay driver
- · High-speed line driver
- High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-500	mA
Static characte	Static characteristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -500 \text{ mA}; T_j = 25 \text{ °C}$		-	1.02	1.4	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



20 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D I
2	S	source	2 🔲 📗 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S S 017aaa259

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMZ950UPEL	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883		

6. Marking

Table 4. Marking codes

Type number	Marking code
PMZ950UPEL	L2

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-500	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-300	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode				'	,
Is	source current	T _{amb} = 25 °C	[1]	-	-350	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

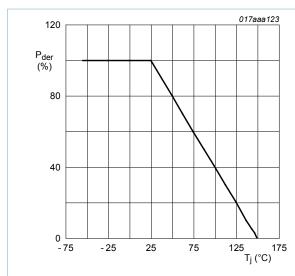


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot}(25^{\circ}C)} \times 100 \%$$

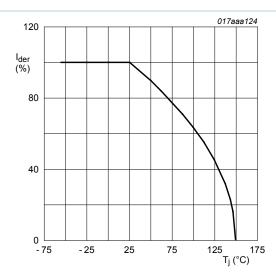


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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20 V, P-channel Trench MOSFET

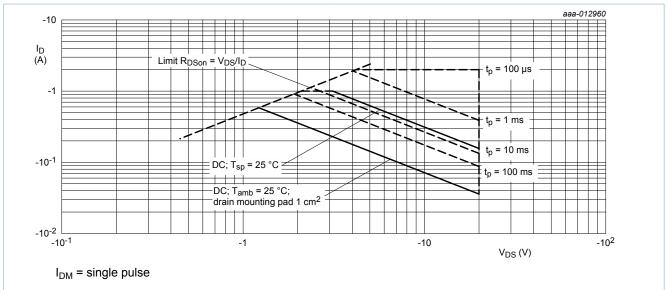


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

8. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f	thermal resistance from junction to ambient		[1]	-	305	360	K/W
			[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

20 V, P-channel Trench MOSFET

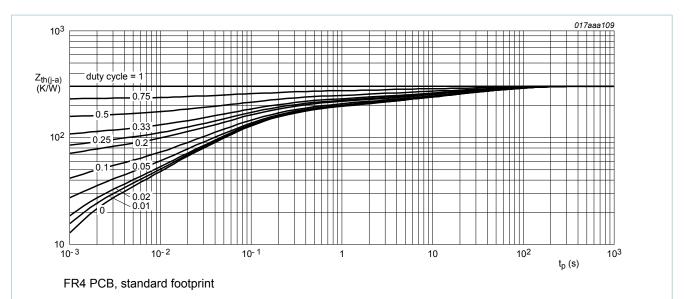


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

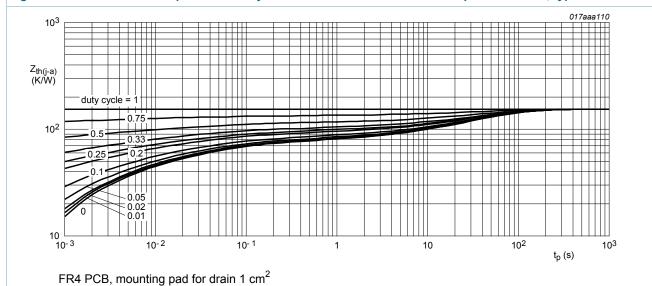


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, P-channel Trench MOSFET

9. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-10	μA
		V _{DS} = -5 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-25	nA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = 1.8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	50	nA
		V _{GS} = -1.8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-50	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_{D} = -500 mA; T_{j} = 25 °C	-	1.02	1.4	Ω
	resistance	V _{GS} = -4.5 V; I _D = -500 mA; T _j = 150 °C	-	1.54	2.1	Ω
		V_{GS} = -2.5 V; I_{D} = -200 mA; T_{j} = 25 °C	-	1.27	2.2	Ω
		V_{GS} = -1.8 V; I_{D} = -40 mA; T_{j} = 25 °C	-	1.7	3.3	Ω
		V_{GS} = -1.5 V; I_{D} = -10 mA; T_{j} = 25 °C	-	2.3	5	Ω
		V_{GS} = -1.2 V; I_{D} = -1 mA; T_{j} = 25 °C	-	3.5	-	Ω
9fs	forward transconductance	V_{DS} = -10 V; I_D = -500 mA; T_j = 25 °C	-	480	-	mS
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_{D} = -450 \text{ mA};$	-	1.19	2.1	nC
Q_{GS}	gate-source charge	V _{GS} = -4.5 V; T _j = 25 °C	-	0.17	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	43	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	14	-	pF
C _{rss}	reverse transfer capacitance		-	8	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -0.45 A; R_{L} = 22 Ω ;	-	2.3	-	ns
t _r	rise time	$V_{GS} = -4.5 \text{ V}; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	5	-	ns
$t_{d(off)}$	turn-off delay time		-	13.5	-	ns

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20 V, P-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _f	fall time			-	6	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I_S = -115 mA; V_{GS} = 0 V; T_j = 25 °C		-	-0.7	-1.2	V

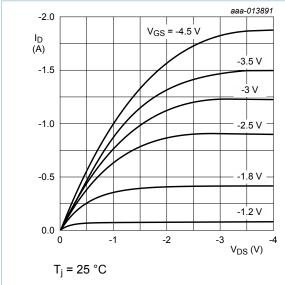


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

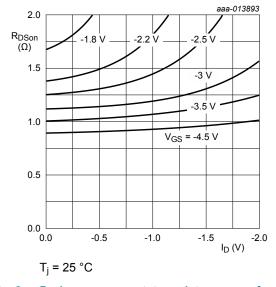


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

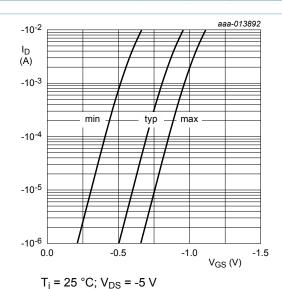


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

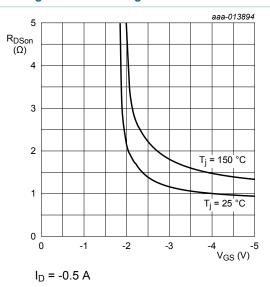


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

20 V, P-channel Trench MOSFET

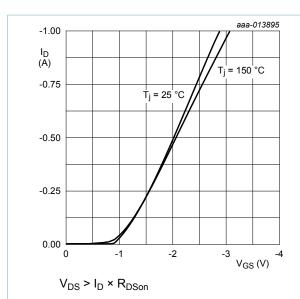


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

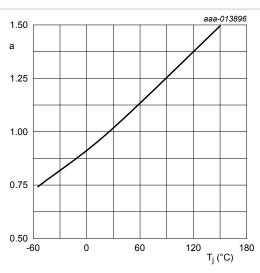


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

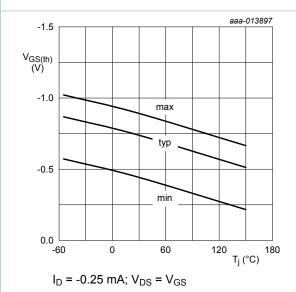


Fig. 12. Gate-source threshold voltage as a function of junction temperature

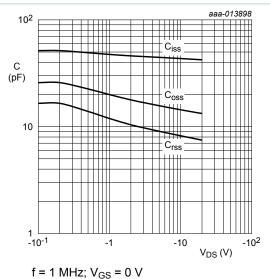


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

20 V, P-channel Trench MOSFET

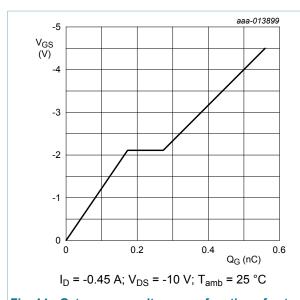


Fig. 14. Gate-source voltage as a function of gate charge; typical values

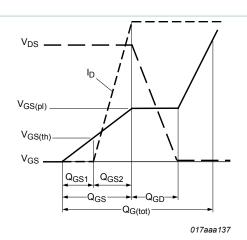


Fig. 15. MOSFET transistor: Gate charge waveform definitions

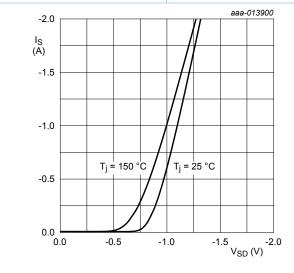
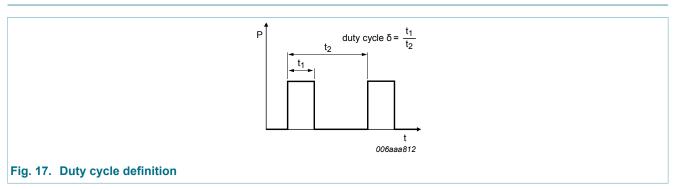


Fig. 16. Source current as a function of source-drain voltage; typical values

10. Test information

 $V_{GS} = 0 V$



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11. Package outline

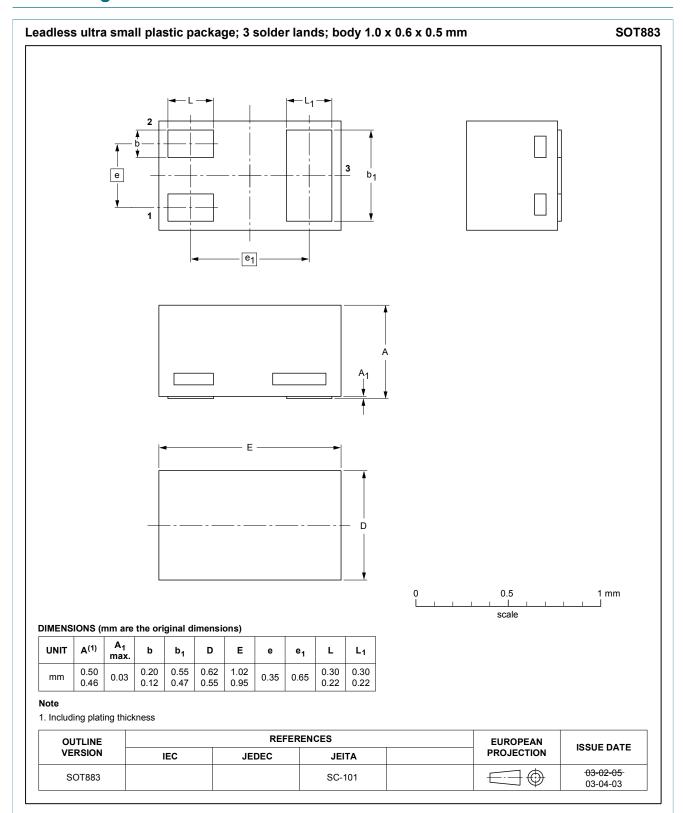


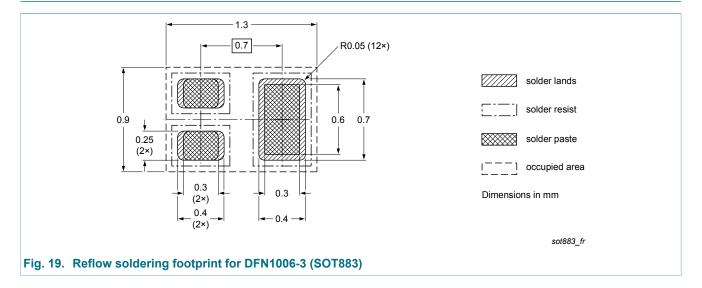
Fig. 18. Package outline DFN1006-3 (SOT883)

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20 V, P-channel Trench MOSFET

12. Soldering



20 V, P-channel Trench MOSFET

13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ950UPEL v.1	20160628	Product data sheet	-	-

20 V, P-channel Trench MOSFET

14. Legal information

14.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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20 V, P-channel Trench MOSFET

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20 V, P-channel Trench MOSFET

15. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Marking	2
7	Limiting values	3
8	Thermal characteristics	4
9	Characteristics	6
10	Test information	9
11	Package outline	10
12	Soldering	11
13	Revision history	
14	Legal information	13
14.1	Data sheet status	13
14.2	Definitions	13
14.3	Disclaimers	13
14.4	Trademarks	14

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15 / 15

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